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REMARKS

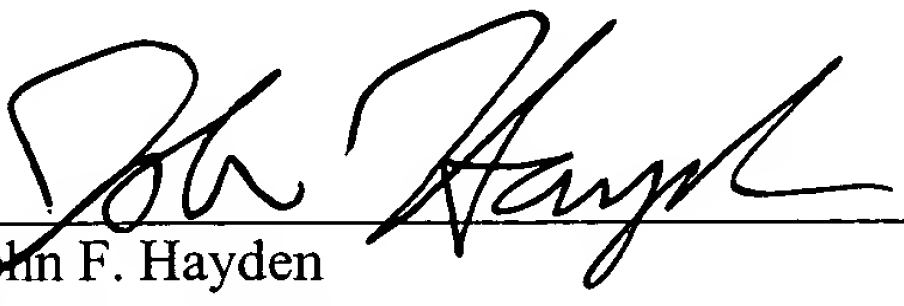
Claims 17-24 and 48-75 are pending in this application, with claims 17, 48, 55, 62 and 69 being independent. Claims 1-16 and 25-47 have been cancelled, claims 17-19 and 21 have been amended, and claims 48-75 have been added.

Applicant hereby elects the invention of Group I, Species 3 (claims 17-24), which are directed to a semiconductor device having a first and second electrode on the first insulating film. Newly added claims 48-75 are also directed to such a device.

A check in the amount of \$400.00 is enclosed for a two-month extension of time. Please apply any other charges or credits to Deposit Account No. 06-1050.

Respectfully submitted,

Date: December 13, 2002



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Version with markings to show changes made

In the claims:

Claims 17-19 and 21 have been amended as follows:

17. (Amended) A semiconductor device comprising:
a first semiconductor layer and a second semiconductor layer on an insulating surface;
a first insulating film on the first semiconductor layer and on the second semiconductor layer;
a first electrode on the first insulating film, overlapping the first semiconductor layer;
a second electrode on the first insulating film, overlapping the second semiconductor layer;
a source wiring on the first insulating film;
a second insulating film covering the first electrode and the source wiring;
a gate wiring on the second insulating film, connected to the first electrode;
a connection electrode on the second insulating film, connected to the source wiring and the first semiconductor layer; and
a pixel electrode on the second insulating film, connected to the first semiconductor layer;
wherein at least one end of the pixel electrode overlays the source wiring with the second insulating film interposed therebetween.

18. (Amended) A device according to claim 17, wherein the first electrode **[overlapping the first semiconductor layer]** is a gate electrode.

19. (Amended) A device according to claim 17, wherein a storage capacitor is formed by the second semiconductor layer **[connected to the pixel electrode, and]**, the second electrode **[connected to a gate wiring of an adjacent pixel, with]**, and the first insulating film **[as a dielectric]**.

21. (Amended) A device according to claim 17, wherein the gate wiring **[is formed from a film having]** comprising an element selected from the group consisting of[:]
polysilicon doped with an impurity element which imparts one conductivity[;], W[;], WSix[;], Al[;], Cu[;], Ta[;], Cr[;], and Mo as its main constituent, and a lamination film of the elements.